CLEAN VERSION OF AMENDED SPECIFICATION PARAGRAPHS

CIRCUIT BOARD PLANE INTERLEAVE APPARATUS AND METHOD
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Paragraph beginning on page 10, line 5:

Several parameters of the physical interface between the interstices 150,160, or tongue/grooves 112/124, 122/114 can also be adjusted. Again, these variations serve most directly to affect the value of capacitance measured between the conductive layers 110, 120, i.e., for the capacitor 95. For example, the separation distance "R" between the tongues 112, 122 can be adjusted. This type of adjustment will inherently affect the spacing "U" between the upper-inner wall of the interstice 160 and the outer wall of the tongue 112, as well as the spacing "L" between the lower-inner wall of the interstice 150 and the outer edge of the tongue 122. However, if such additional changes are undesired, then the thickness T1, T2 of the tongues 112, 122 may also be adjusted to compensate for the relative movement brought about by varying the separation distance "R".

Paragraph beginning on page 14, line 3:

As mentioned previously, there is no ultimate limit, other than practicality (e.g. overall cost, manufacturing processes complexity, time required, etc.), to the number of interstices, or the shape of the interstices or tongues/grooves, used for engagement between the conductive layer 110 and the conductive layer 120. For example, as can be seen in Figure 9, a plurality of grooves 165 formed in the first conductive layer 110 can be seen engaging a plurality of tongues 170 formed in the conductive layer 120. A plurality of tongues 180 is also formed in the first conductive layer 110, which overlap the tongues 170 of the second conductive layer 120, and engage the grooves 155. However, in this case, while the shape of the grooves 165 complements the shape of the tongues 170, and the shape of the grooves 155 complements the shape of the tongues 180, the shapes of the interstices 150, 160 are non-complementary, and different than any other heretofore discussed. Here some of the interstices are formed into U shapes (interstices 160), and some of the interstices are formed into box or square shapes (interstices 150). Thus, instead of characterizing the shape of the interstices 150, 160 with any particular dimensions, or ratios of dimensions (e.g., the depth D1 is twice as deep as the width H1, or the tongue thickness T1 is one-third of the width H1), it may also be useful to characterize the shape of individual interstices as that of commonly known geometric shapes or alphabetic characters,

such as U shaped, triangular shaped, square shaped, elliptically or oval shaped, etc.

Paragraph beginning on page 25, line 17:

After the first set of interstices or grooves are formed in block 430, the second interstice, or second plurality of interstices can be formed (and if desired at this time, engaged with the first interstice, or first plurality of interstices), according to block 440. If the tongue and groove approach is taken, then one or more tongues can now be formed in the second conductive layer, so as to engage the corresponding grooves in the first conductive layer. In either case, the second set of interstices or tongues will be formed according to the shapes chosen in block 400, and whether complementary shapes were chosen (block 410) or non-complementary shapes were chosen (block 420). The size of the second set of interstices, or the tongues formed in the second conductive layer will usually be determined by the size of the first set of interstices, or grooves, formed in the first conductive layer in accordance with block 430, along with the materials selected for the first and second conductive layers, and the dielectric layer (see blocks 470 and 480).